

Silicon PNP Power Transistor

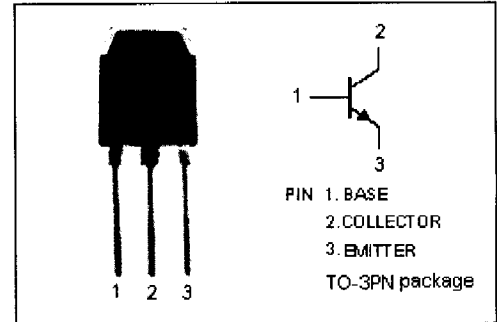
MJW21191

DESCRIPTION

- DC Current Gain Specified up to 8.0 Amperes at Temperature
- High SOA: 20 A, 18 V, 100 ms
- TO-3PN Package
- Complement to Type MJW21192

APPLICATIONS

- designed for power audio output, or high power drivers in audio amplifiers applications

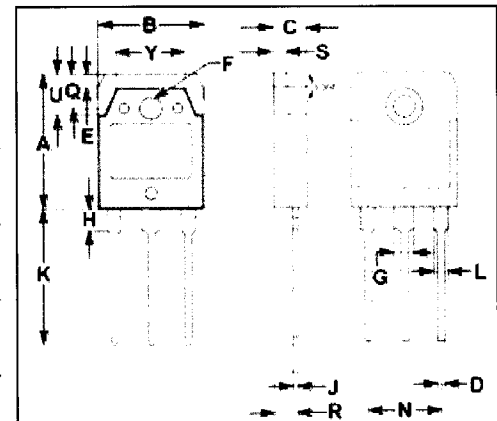


ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-Base Voltage	150	V
V _{CE0}	Collector-Emitter Voltage	150	V
V _{EB0}	Emitter-Base Voltage	5	V
I _C	Collector Current-Continuous	8	A
I _{CM}	Collector Current-Pulse	16	A
I _B	Base Current-Continuous	2	A
P _C	Collector Power Dissipation @ T _C =25°C	100	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C

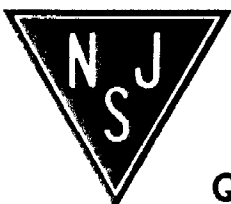
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	0.65	°C/W
R _{th j-a}	Thermal Resistance, Junction to Ambient	50	°C/W



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.38	15.42
C	4.75	4.85
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.98	3.02
H	3.20	3.40
J	0.595	0.605
K	19.95	20.25
L	1.98	2.02
N	10.89	10.91
Q	4.95	5.05
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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Silicon PNP Power Transistor**MJW21191****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 10mA ; I _B = 0	150			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 0.4A			1.0	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 8A; I _B = 1.6A			2.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 4A; V _{CE} = 2V			2.0	V
I _{CES}	Collector Cutoff Current	V _{CB} = 250V; I _E = 0			10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μ A
h _{FE-1}	DC Current Gain	I _C = 4A ; V _{CE} = 2V	15		100	
h _{FE-2}	DC Current Gain	I _C = 8A ; V _{CE} = 2V	5.0			
f _T	Current-Gain—Bandwidth Product	I _E = 1A ; V _{CE} = 10V	4			MHz